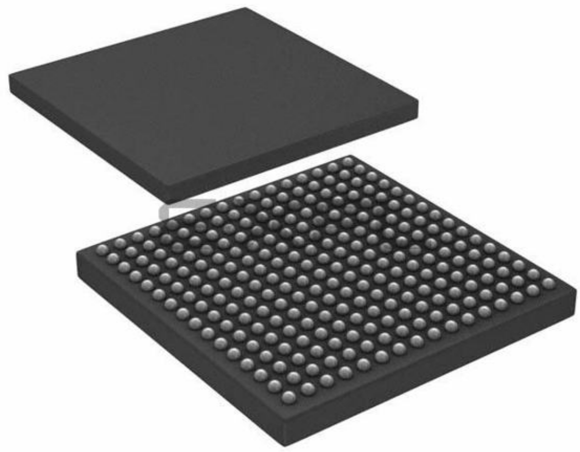

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	9216
Total RAM Bits	55296
Number of I/O	178
Number of Gates	400000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl400v2-fg256t

field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOO family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOO architecture provides granularity comparable to standard-cell ASICs. The IGLOO device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4 and Figure 1-2 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory†
- Extensive CCCs and PLLs†
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC® family of third-generation-architecture flash FPGAs.

† *The AGL015 and AGL030 do not support PLL or SRAM.*

Flash*Freeze Technology

The IGLOO device has an ultra-low power static mode, called Flash*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash*Freeze technology enables the user to quickly (within 1 µs) enter and exit Flash*Freeze mode by activating the Flash*Freeze pin while all power supplies are kept at their original values. In addition, I/Os and global I/Os can still be driven and can be toggling without impact on power consumption, clocks can still be driven or can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and states. I/O states are tristated during Flash*Freeze mode or can be set to a certain state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL, and the device consumes as little as 5 µW in this mode.

Flash*Freeze technology allows the user to switch to active mode on demand, thus simplifying the power management of the device.

The Flash*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. It is also possible to use the Flash*Freeze pin as a regular I/O if Flash*Freeze mode usage is not planned, which is advantageous because of the inherent low power static (as low as 12 µW) and dynamic capabilities of the IGLOO device. Refer to Figure 1-3 for an illustration of entering/exiting Flash*Freeze mode.

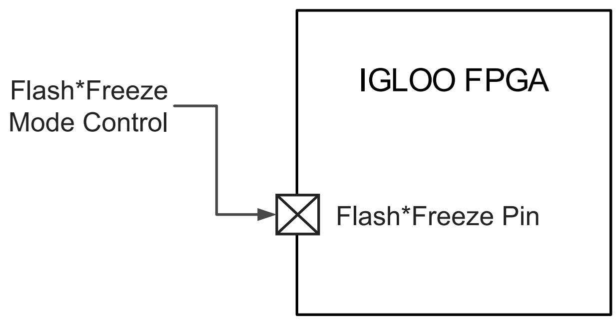

Figure 1-3 • **IGLOO Flash*Freeze Mode**

VersaTiles

The IGLOO core consists of VersaTiles, which have been enhanced beyond the ProASIC<u>PLUS</u>® core tiles. The IGLOO VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-4 for VersaTile configurations.

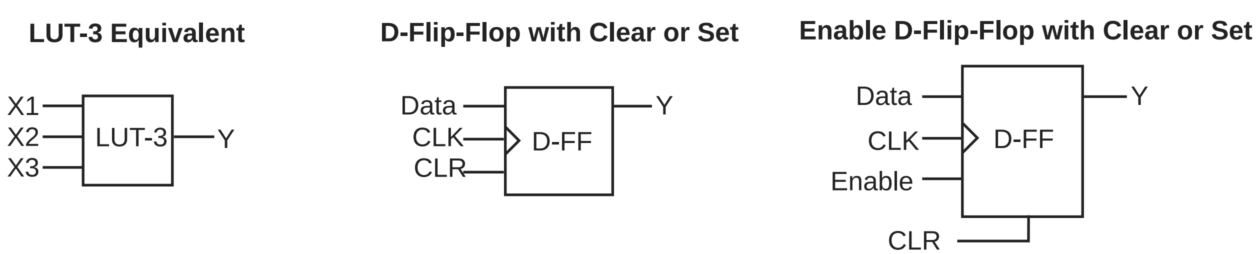

Figure 1-4 • **VersaTile Configurations**

Table 2-3 • **Flash Programming Limits – Retention, Storage, and Operating Temperature**[1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 on page 2-2 for device operating conditions and absolute limits.*

Table 2-4 • **Overshoot and Undershoot Limits** [1]

VCCI	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle[2]	Maximum Overshoot/ Undershoot[2]
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. *Based on reliability requirements at junction temperature at 85°C.*
2. *The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.*
3. *This table does not provide PCI overshoot/undershoot limits.*

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every IGLOO device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

IGLOO I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points (Figure 2-1 on page 2-4 and Figure 2-2 on page 2-5).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI **Trip Point:**
Ramping up (V5 devices): 0.6 V < trip_point_up < 1.2 V
Ramping down (V5 Devices): 0.5 V < trip_point_down < 1.1 V
Ramping up (V2 devices): 0.75 V < trip_point_up < 1.05 V
Ramping down (V2 devices): 0.65 V < trip_point_down < 0.95 V

VCC **Trip Point:**
Ramping up (V5 devices): 0.6 V < trip_point_up < 1.1 V
Ramping down (V5 devices): 0.5 V < trip_point_down < 1.0 V

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja}. The thermal characteristics for θ_{ja} are shown for two air flow rates. The absolute maximum junction temperature is 100°C. EQ 2 shows a sample calculation of the absolute maximum power dissipation allowed for the AGL1000-FG484 package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. } (°C) - \text{Max. ambient temp. } (°C)}{\theta_{ja}(°C/W)} = \frac{100°C - 70°C}{23.3°C/W} = 1.28\ W$$

EQ 2

Table 2-5 • **Package Thermal Resistivities**

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Unit
				Still Air	1 m/s	2.5 m/s	
Quad Flat No Lead (QN)	AGL030	132	13.1	21.4	16.8	15.3	C/W
	AGL060	132	11.0	21.2	16.6	15.0	C/W
	AGL125	132	9.2	21.1	16.5	14.9	C/W
	AGL250	132	8.9	21.0	16.4	14.8	C/W
	AGL030	68	13.4	68.4	45.8	43.1	C/W
Very Thin Quad Flat Pack (VQ)*		100	10.0	35.3	29.4	27.1	C/W
Chip Scale Package (CS)	AGL1000	281	6.0	28.0	22.8	21.5	C/W
	AGL400	196	7.2	37.1	31.1	28.9	C/W
	AGL250	196	7.6	38.3	32.2	30.0	C/W
	AGL125	196	8.0	39.5	33.4	31.1	C/W
	AGL030	81	12.4	32.8	28.5	27.2	C/W
	AGL060	81	11.1	28.8	24.8	23.5	C/W
	AGL250	81	10.4	26.9	22.3	20.9	C/W
Micro Chip Scale Package (UC)	AGL030	81	16.9	40.6	35.2	33.7	C/W
Fine Pitch Ball Grid Array (FG)	AGL060	144	18.6	55.2	49.4	47.2	C/W
	AGL1000	144	6.3	31.6	26.2	24.2	C/W
	AGL400	144	6.8	37.6	31.2	29.0	C/W
	AGL250	256	12.0	38.6	34.7	33.0	C/W
	AGL1000	256	6.6	28.1	24.4	22.7	C/W
	AGL1000	484	8.0	23.3	19.0	16.7	C/W

*Note: *Thermal resistances for other device-package combinations will be posted in a later revision.*

Disclaimer:

The simulation for determining the junction-to-air thermal resistance is based on JEDEC standards (JESD51) and assumptions made in building the model. Junction-to-case is based on SEMI G38-88. JESD51 is only used for comparing one package to another package, provided the two tests uses the same condition. They have little relevance in actual application and therefore should be used with a degree of caution.

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode*

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: $IDD = N_{BANKS} \times ICCI$. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode

	Core Voltage	AGL015	AGL030	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	µA

Table 2-12 • Quiescent Supply Current (IDD), No IGLOO Flash*Freeze Mode[1]

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
ICCA Current[2]										
Typical (25°C)	1.2 V	5	6	10	13	18	25	28	42	µA
	1.5 V	14	16	20	28	44	66	82	137	µA
ICCI or IJTAG Current[3]										
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *$IDD = N_{BANKS} \times ICCI + ICCA$. JTAG counts as one bank when powered.*
2. *Includes VCC, VPUMP, and VCCPLL currents.*
3. *Values do not include I/O static contribution (PDC6 and PDC7).*

Table 2-17 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] Applicable to Standard Plus I/O Banks**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	122.16
3.3 V LVCMOS Wide Range[4]	5	3.3	–	122.16
2.5 V LVCMOS	5	2.5	–	68.37
1.8 V LVCMOS	5	1.8	–	34.53
1.5 V LVCMOS (JESD8-11)	5	1.5	–	23.66
1.2 V LVCMOS[5]	5	1.2	–	14.90
1.2 V LVCMOS Wide Range[5]	5	1.2	–	14.90
3.3 V PCI	10	3.3	–	181.06
3.3 V PCI-X	10	3.3	–	181.06

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *P_{DC7} is the static power (where applicable) measured on VCCI.*
3. *P_{AC10} is the total dynamic power measured on VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
5. *Applicable for IGLOO V2 devices only.*

Table 2-18 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] Applicable to Standard I/O Banks**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC7 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	–	104.38
3.3 V LVCMOS Wide Range[4]	5	3.3	–	104.38
2.5 V LVCMOS	5	2.5	–	59.86
1.8 V LVCMOS	5	1.8	–	31.26
1.5 V LVCMOS (JESD8-11)	5	1.5	–	21.96
1.2 V LVCMOS[5]	5	1.2	–	13.49
1.2 V LVCMOS Wide Range[5]	5	1.2	–	13.49

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC7 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
5. *Applicable for IGLOO V2 devices only.*

Table 2-31 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	5	–	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
2.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	1.08	0.66	2.14	1.83	2.73	2.93	5.73	5.43	ns
1.8 V LVCMOS	12 mA	12	High	5	–	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
1.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
3.3 V PCI	Per PCI spec	–	High	10	25[2]	0.97	2.32	0.18	0.74	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[2]	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
LVDS	24 mA	–	High	–	–	0.97	1.74	0.19	1.35	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.97	1.68	0.19	1.16	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-32 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Standard Plus I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	5	–	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns
2.5 V LVCMOS	12 mA	12	High	5	–	0.97	1.75	0.18	1.08	0.66	1.79	1.52	2.38	2.70	5.39	5.11	ns
1.8 V LVCMOS	8 mA	8	High	5	–	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
1.5 V LVCMOS	4 mA	4	High	5	–	0.97	2.25	0.18	1.18	0.66	2.30	2.00	2.53	2.68	5.89	5.59	ns
3.3 V PCI	Per PCI spec	–	High	10	25 [2]	0.97	1.97	0.18	0.73	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 [2]	0.97	1.97	0.19	0.70	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-44 • **I/O Short Currents IOSH/IOSL Applicable to Standard I/O Banks**

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
1.5 V LVCMOS	2 mA	13	16
1.2 V LVCMOS	1 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26

Note: $*T_J = 100°C$

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-45 • **Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
–20°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

Table 2-46 • **I/O Input Rise Time, Fall Time, and Related I/O Reliability1**

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS	No requirement	10 ns *	20 years (100°C)
LVDS/B-LVDS/M-LVDS/ LVPECL	No requirement	10 ns *	10 years (100°C)

Note: The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.

Table 2-77 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI = 2.7 Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	4 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	6 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns
100 µA	8 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-78 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	4 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	6 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
100 µA	8 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Applies to 1.2 V Core Voltage

Table 2-89 • **2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
4 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
6 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
8 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
12 mA	Std.	1.55	4.17	0.26	1.20	1.10	4.23	3.99	3.30	3.67	10.02	9.77	ns
16 mA	Std.	1.55	3.98	0.26	1.20	1.10	4.04	3.88	3.34	3.76	9.83	9.66	ns
24 mA	Std.	1.55	3.90	0.26	1.20	1.10	3.96	3.90	3.40	4.09	9.75	9.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-90 • **2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
4 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
6 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
8 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
12 mA	Std.	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
16 mA	Std.	1.55	2.59	0.26	1.20	1.10	2.63	2.24	3.34	3.88	8.41	8.03	ns
24 mA	Std.	1.55	2.60	0.26	1.20	1.10	2.64	2.18	3.40	4.22	8.42	7.97	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-91 • **2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
4 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
6 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
8 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
12 mA	Std.	1.55	3.66	0.26	1.19	1.10	3.71	3.55	2.94	3.41	9.50	9.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer. Furthermore, all LVCMOS 1.2 V software macros comply with LVCMOS 1.2 V wide range as specified in the JESD8-12A specification.

Table 2-127 • **Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-128 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks**

1.2 V LVCMOS	VIL		VIH		VOL	VOH	I_{OL}	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-129 • **Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks**

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	μA[4]	μA[4]
1 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	20	26	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

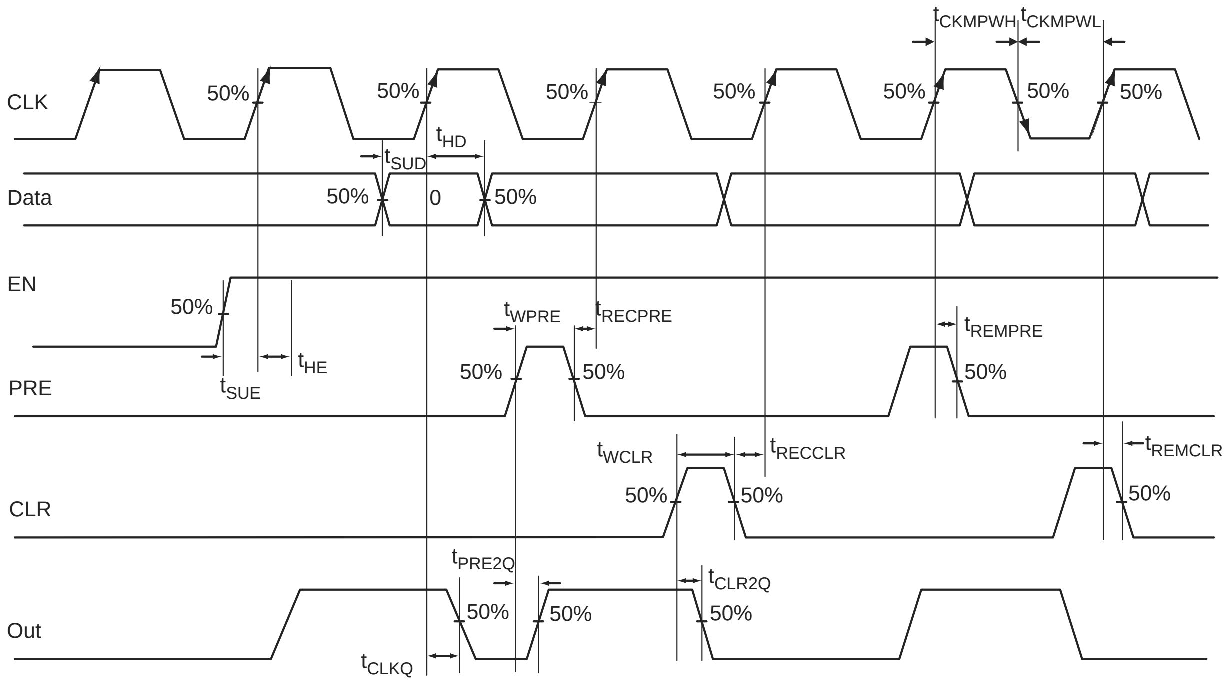

Figure 2-28 • **Timing Model and Waveforms**

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-171 •* Register Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t_{SUD}	Data Setup Time for the Core Register	0.81	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.73	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width High for the Core Register	0.56	ns
t_{CKMPWL}	Clock Minimum Pulse Width Low for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-179 • AGL600 Global Resource Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std. Min.[1]	Std. Max.[2]	Units
t_{RCKL}	Input Low Delay for Global Clock	1.48	1.82	ns
t_{RCKH}	Input High Delay for Global Clock	1.52	1.94	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-180 • AGL1000 Global Resource Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std. Min.[1]	Std. Max.[2]	Units
t_{RCKL}	Input Low Delay for Global Clock	1.55	1.89	ns
t_{RCKH}	Input High Delay for Global Clock	1.60	2.02	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.42	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-195 **• FIFO**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.99	ns
t_{ENH}	REN, WEN Hold Time	0.16	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.76	ns
t_{DH}	Input Data (WD) Hold Time	0.25	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.33	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.80	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	3.53	ns
t_{WCKFF}	WCLK High to Full Flag Valid	3.35	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	12.85	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	3.48	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	12.72	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	2.02	ns
	RESET Low to Data Out Low on RD (pipelined)	2.02	ns
$t_{REMRSTB}$	RESET Removal	0.61	ns
$t_{RECRSTB}$	RESET Recovery	3.21	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO a devices. The Flash*Freeze pin location is independent of device, allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO FPGA Fabric User Guide* for more information on I/O states during Flash*Freeze mode.

***Table 3-1* • Flash*Freeze Pin Location in IGLOO Family Packages (device-independent)**

IGLOO Packages	Flash*Freeze Pin
CS81/UC81	H2
CS121	J5
CS196	P3
CS281	W2
QN48	14
QN68	18
QN132	B12
VQ100	27
FG144	L3
FG256	T3
FG484	W6

CS196	
Pin Number	AGL125 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO09RSB0
A6	IO15RSB0
A7	IO18RSB0
A8	IO22RSB0
A9	IO27RSB0
A10	GBC0/IO35RSB0
A11	GBB0/IO37RSB0
A12	GBB1/IO38RSB0
A13	GBA1/IO40RSB0
A14	GND
B1	VCCIB1
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO16RSB0
B7	IO20RSB0
B8	IO24RSB0
B9	IO28RSB0
B10	GND
B11	GBC1/IO36RSB0
B12	GBA0/IO39RSB0
B13	GBA2/IO41RSB0
B14	GBB2/IO43RSB0
C1	GAC2/IO128RSB1
C2	GAB2/IO130RSB1
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO14RSB0
C7	VCCIB0
C8	NC

CS196	
Pin Number	AGL125 Function
C9	IO23RSB0
C10	IO29RSB0
C11	VCCIB0
C12	IO42RSB0
C13	GNDQ
C14	IO44RSB0
D1	IO127RSB1
D2	IO129RSB1
D3	GAA2/IO132RSB1
D4	IO126RSB1
D5	IO06RSB0
D6	IO13RSB0
D7	IO19RSB0
D8	IO21RSB0
D9	IO26RSB0
D10	IO31RSB0
D11	IO30RSB0
D12	VMV0
D13	IO46RSB0
D14	GBC2/IO45RSB0
E1	IO125RSB1
E2	GND
E3	IO131RSB1
E4	VCCIB1
E5	NC
E6	IO08RSB0
E7	IO17RSB0
E8	IO12RSB0
E9	IO11RSB0
E10	NC
E11	VCCIB0
E12	IO32RSB0
E13	GND
E14	IO34RSB0
F1	IO124RSB1
F2	IO114RSB1

CS196	
Pin Number	AGL125 Function
F3	IO113RSB1
F4	IO112RSB1
F5	IO111RSB1
F6	NC
F7	VCC
F8	VCC
F9	NC
F10	IO07RSB0
F11	IO25RSB0
F12	IO10RSB0
F13	IO33RSB0
F14	IO47RSB0
G1	GFB1/IO121RSB1
G2	GFA0/IO119RSB1
G3	GFA2/IO117RSB1
G4	VCOMPLF
G5	GFC0/IO122RSB1
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO52RSB0
G11	GCB1/IO53RSB0
G12	GCA0/IO56RSB0
G13	IO48RSB0
G14	GCC2/IO59RSB0
H1	GFB0/IO120RSB1
H2	GFA1/IO118RSB1
H3	VCCPLF
H4	GFB2/IO116RSB1
H5	GFC1/IO123RSB1
H6	VCC
H7	GND
H8	GND
H9	VCC
H10	GCC1/IO51RSB0

FG484	
Pin Number	**AGL400 Function**
V15	IO85RSB2
V16	GDB2/IO81RSB2
V17	TDI
V18	NC
V19	TDO
V20	GND
V21	NC
V22	NC
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO126RSB2
W6	FF/GEB2/IO133RSB2
W7	IO124RSB2
W8	IO116RSB2
W9	IO113RSB2
W10	IO107RSB2
W11	IO105RSB2
W12	IO102RSB2
W13	IO97RSB2
W14	IO92RSB2
W15	GDC2/IO82RSB2
W16	IO86RSB2
W17	GDA2/IO80RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	NC
Y3	NC
Y4	NC
Y5	GND
Y6	NC

FG484	
Pin Number	**AGL1000 Function**
G5	IO222PDB3
G6	GAC2/IO223PDB3
G7	IO223NDB3
G8	GNDQ
G9	IO23RSB0
G10	IO29RSB0
G11	IO33RSB0
G12	IO46RSB0
G13	IO52RSB0
G14	IO60RSB0
G15	GNDQ
G16	IO80NDB1
G17	GBB2/IO79PDB1
G18	IO79NDB1
G19	IO82NPB1
G20	IO85PDB1
G21	IO85NDB1
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO217PDB3
H5	IO218PDB3
H6	IO221NDB3
H7	IO221PDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO38RSB0
H12	IO47RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO80PDB1
H17	IO83PPB1
H18	IO86PPB1

FG484	
Pin Number	**AGL1000 Function**
U1	IO195PDB3
U2	IO195NDB3
U3	IO194NPB3
U4	GEB1/IO189PDB3
U5	GEB0/IO189NDB3
U6	VMV2
U7	IO179RSB2
U8	IO171RSB2
U9	IO165RSB2
U10	IO159RSB2
U11	IO151RSB2
U12	IO137RSB2
U13	IO134RSB2
U14	IO128RSB2
U15	VMV1
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO113NDB1
U20	NC
U21	IO108NDB1
U22	IO109PDB1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO188PDB3
V5	GEA0/IO188NDB3
V6	IO184RSB2
V7	GEC2/IO185RSB2
V8	IO168RSB2
V9	IO163RSB2
V10	IO157RSB2
V11	IO149RSB2
V12	IO143RSB2
V13	IO138RSB2
V14	IO131RSB2